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TECHNOLOGY CENTER 2800

April 9, 2003

VIA FACSIMILE

To: Examiner Douglas A. Wille
Group Art Unit No. 2814
U.S.P.T.O.

Facsimile No.: (703) 872-9319

From: Peter A. Balnave

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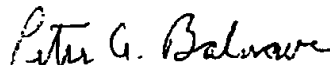
Re: Enclosed § 1.116 Amendment
U.S. Patent Application Serial No. 09/988,060
Docket No. F01-273-US DIV

Dear Examiner Wille:

We are enclosing an After-Final Amendment for the above-referenced patent application.

Thank you in advance for your consideration on this case.

Very truly yours,



Peter A. Balnave, Ph.D.

PAB/geb
Enclosures

Total No. of Pages Transmitted: 6

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EXPEDITED PROCEDURE
UNDER 37 C.F.R. 1.116

M. Baunson
7/14/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Toshiya UEMURA et al.

Serial No.: 09/988,060

Group Art Unit: 2814

Filed: November 16, 2001

Examiner: Douglas A. Wille

For: A SEMICONDUCTOR LIGHT-EMITTING ELEMENT

Honorable Commissioner of Patents
Washington, D.C. 20231
Box AF

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AMENDMENT UNDER 37 C.F.R. §1.116

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Sir:

In response to the Final Office Action dated January 10, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 2 as follows:

1. (Amended) A semiconductor light-emitting element comprising:
a chip having at least an electrode and a protective film layer;
an insulating resin for sealing said chip;
wherein said insulating resin is hardened at high temperature and heat-treated in an atmosphere having relative humidity at a temperature of 60° C or higher.
2. (Amended) A semiconductor light-emitting element according to claim 1, wherein the heat treatment is performed at any temperature in a range from 60° C to 100° C.